







DLP670RE DLPS241 - APRIL 2023

DLP670RE 0.67 WUXGA DMD

1 Features

- · 0.67-inch micromirror array diagonal
 - WUXGA (1920 × 1200)
 - 7.56-micron micromirror pitch
 - ± 12° micromirror tilt angle (relative to flat state)
 - Corner illumination
- 2xLVDS input data bus
- The DLP670RE chipset includes:
 - DLP670RE DMD
 - DLPC4430 controller
 - DLPA100 controller power management and motor driver IC

2 Applications

- **WUXGA** display
- Smart display
- Digital signage
- **Business projector**
- Education projector

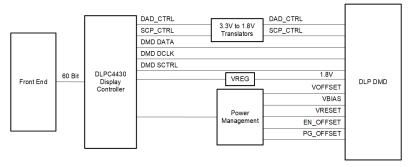
3 Description

The TI DLP670RE digital micromirror device (DMD) is a digitally controlled micro-electromechanical system (MEMS) spatial light modulator (SLM) that enables bright, affordable DLP® 0.67 WUXGA display solutions. The DLP670RE DMD, together with the DLPC4430 display controller, the DLPA100 controller power and motor driver provides the capability to achieve high performance systems and is a great fit for display applications that require higher resolution and 16:10 aspect ratio, high brightness, and system simplicity.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
DLP670RE	FYE (350)	35.0 mm × 32.2 mm × 5.1 mm

For all available packages, see the orderable addendum at the end of the datasheet.



DLP670LE Simplified Application



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4 Revision History

Date	Revision	Note
April 2023	*	Initial Release



5 Pin Configuration and Functions

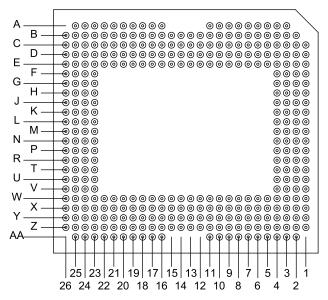


Figure 5-1. FYE Package 350-Pin Bottom View

Table 5-1. Pin Functions

Table 3-1. Fill Full Culons											
PIN ⁽¹⁾		TYPE ⁽⁵⁾	SIGNAL	DATA	INTERNAL	DESCRIPTION	TRACE (mils) ⁽⁴⁾				
NAME	NO.		0.0.0.	RATE ⁽²⁾ TERM ⁽³⁾			110102 (11110)				
	DATA BUS A										
D_AN(0)	B14	I		DDR	Differential	Data, negative	494.88				
D_AN(1)	B15	I		DDR	Differential	Data, negative	486.18				
D_AN(2)	C16	I		DDR	Differential	Data, negative	495.16				
D_AN(3)	K24	I		DDR	Differential	Data, negative	485.67				
D_AN(4)	B18	I		DDR	Differential	Data, negative	494.76				
D_AN(5)	L24	I		DDR	Differential	Data, negative	490.63				
D_AN(6)	C19	I		DDR	Differential	Data, negative	495.16				
D_AN(7)	H24	I	LVDS	DDR	Differential	Data, negative	485.55				
D_AN(8)	H23	I	LVD3	DDR	Differential	Data, negative	495.16				
D_AN(9)	B25	I		DDR	Differential	Data, negative	485.59				
D_AN(10)	D24	I		DDR	Differential	Data, negative	495.16				
D_AN(11)	E25	I		DDR	Differential	Data, negative	495.16				
D_AN(12)	F25	I		DDR	Differential	Data, negative	490.04				
D_AN(13)	H25	I		DDR	Differential	Data, negative	485.91				
D_AN(14)	L25	I		DDR	Differential	Data, negative	495.16				
D_AN(15)	G24	I		DDR	Differential	Data, negative	495.16				



PIN ⁽¹⁾			Table 5-	DATA	INTERNAL		
NAME	NO.	TYPE ⁽⁵⁾	SIGNAL	RATE ⁽²⁾	TERM ⁽³⁾	DESCRIPTION	TRACE (mils) ⁽⁴⁾
D AP(0)	C14	I		DDR	Differential	Data, positive	494.84
D_AP(1)	B16	ı		DDR	Differential	Data, positive	486.22
D_AP(2)	C17	ı		DDR	Differential	Data, positive	494.65
D_AP(3)	K23	ı		DDR	Differential	Data, positive	488.42
D_AP(4)	B19	ı		DDR	Differential	Data, positive	495.16
D_AP(5)	L23	ı		DDR	Differential	Data, positive	490.67
D_AP(6)	C20	ı		DDR	Differential	Data, positive	498.11
D_AP(7)	J24	ı		DDR	Differential	Data, positive	486.22
D_AP(8)	J23	ı	LVDS	DDR	Differential	Data, positive	495.47
D_AP(9)	C25	ı		DDR	Differential	Data, positive	485.94
D_AP(10)	E24	ı		DDR	Differential	Data, positive	495.16
D_AP(11)	D25	I		DDR	Differential	Data, positive	494.13
D_AP(12)	G25	ı		DDR	Differential	Data, positive	488.98
D_AP(13)	J25	I		DDR	Differential	Data, positive	492.56
D_AP(14)	K25	I		DDR	Differential	Data, positive	495.16
D_AP(15)	F24	I		DDR	Differential	Data, positive	495.16
				DATA	A BUS B		
D_BN(0)	Z14	I		DDR	Differential	Data, negative	494.92
D_BN(1)	Z15	I		DDR	Differential	Data, negative	486.18
D_BN(2)	Y16	I		DDR	Differential	Data, negative	496.46
D_BN(3)	P24	I		DDR	Differential	Data, negative	493.74
D_BN(4)	Z18	I		DDR	Differential	Data, negative	494.76
D_BN(5)	N24	I		DDR	Differential	Data, negative	495.16
D_BN(6)	Y19	I		DDR	Differential	Data, negative	492.16
D_BN(7)	T24	I	17/20	DDR	Differential	Data, negative	492.68
D_BN(8)	T23	I	LVDS	DDR	Differential	Data, negative	484.45
D_BN(9)	Z25	1		DDR	Differential	Data, negative	492.09
D_BN(10)	X24	1		DDR	Differential	Data, negative	497.72
D_BN(11)	W25	I		DDR	Differential	Data, negative	495.16
D_BN(12)	V25	I		DDR	Differential	Data, negative	484.17
D_BN(13)	T25	I		DDR	Differential	Data, negative	481.42
D_BN(14)	N25	1		DDR	Differential	Data, negative	495.16
D_BN(15)	U24	ı		DDR	Differential	Data, negative	489.8



Table 5-1. Pin Functions (continued)								
	NO	TYPE ⁽⁵⁾	SIGNAL	DATA RATE ⁽²⁾	INTERNAL TERM ⁽³⁾	DESCRIPTION	TRACE (mils) ⁽⁴⁾	
NAME	NO.					Data mastria	40.4.00	
D_BP(0)	Y14	I		DDR	Differential	Data, positive	494.88	
D_BP(1)	Z16	l		DDR	Differential	Data, positive	486.26	
D_BP(2)	Y17	l		DDR	Differential	Data, positive	495.16	
D_BP(3)	P23	l		DDR	Differential	Data, positive	492.48	
D_BP(4)	Z19	I		DDR	Differential	Data, positive	495.16	
D_BP(5)	N23	I		DDR	Differential	Data, positive	497.99	
D_BP(6)	Y20	I		DDR	Differential	Data, positive	495.16	
D_BP(7)	R24	I	LVDS	DDR	Differential	Data, positive	492.05	
D_BP(8)	R23	I		DDR	Differential	Data, positive	484.45	
D_BP(9)	Y25	I		DDR	Differential	Data, positive	492.24	
D_BP(10)	W24	1		DDR	Differential	Data, positive	495.16	
D_BP(11)	X25	1		DDR	Differential	Data, positive	494.72	
D_BP(12)	U25	I		DDR	Differential	Data, positive	483.78	
D_BP(13)	R25	I		DDR	Differential	Data, positive	489.13	
D_BP(14)	P25	I		DDR	Differential	Data, positive	499.53	
D_BP(15)	V24	I		DDR	Differential	Data, positive	488.66	
				SERIAL	CONTROL			
SCTRL_AN	C23	I		DDR	Differential	Serial control, negative	492.95	
SCTRL_BN	Y23	I	LV/DC	DDR	Differential	Serial control, negative	493.78	
SCTRL_AP	C24	I	LVDS	DDR	Differential	Serial control, negative	493.78	
SCTRL_BP	Y24	I		DDR	Differential	Serial control, negative	493.11	
	_			CL	оскѕ			
DCLK_AN	B23	I			Differential	Clock, negative	480.35	
DCLK_BN	Z23	I	1.450		Differential	Clock, negative	486.22	
DCLK_AP	B22	I	LVDS		Differential	Clock, negative	485.83	
DCLK_BP	Z22	I			Differential	Clock, negative	491.93	
			SERIAL	COMMUNI	CATIONS PORT ((SCP)		
SCP_DO	B8	0		SDR		Serial communications port output		
SCP_DI	B7	I		SDR		Serial communication port data I		
SCP_CLK	В6	ı	LVCMOS		Pulldown	Serial communications port clock		
SCP_ENZ	C8	I				Active-low serial communications port enable		
	_		MICF	OMIRROR	RESET CONTRO	DL		



Table 5-1. Pin Functions (continued)

PIN ⁽¹⁾	PIN(1) DATA INTERNAL PERCENTION TRACE (1911-1/41)							
NAME	NO.	TYPE ⁽⁵⁾	SIGNAL	RATE ⁽²⁾	TERM ⁽³⁾	DESCRIPTION	TRACE (mils) ⁽⁴⁾	
RESET_ADDR(0)	X9	ı				Reset driver address select		
RESET_ADDR(1)	X8	1				Reset driver address select		
RESET_ADDR(2)	Z8	1				Reset driver address select		
RESET_ADDR(3)	Z 7	1	LVCMOS		Pulldown	Reset driver address select		
RESET_MODE(0)	W11	I	LVOIVIOO		T undown	Reset driver mode select		
RESET_MODE(1)	Z10	I				Reset driver mode select		
RESET_SEL(0)	Y10	I				Reset driver level select		
RESET_SEL(1)	Y9	I				Reset driver level select		
RESET_STROBE	Y7	I				Reset address, mode, and level latched on rising-edge		
			EN	IABLES AN	ID INTERRUPTS			
PWRDNZ	D2	1			Pulldown	Active-low device reset		
RESET_OEZ	W7	I			Pulldown	Active-low output enable for DMD reset driver circuits		
RESETZ	Z6	I	LVCMOS		Pulldown	Active-low sets reset circuits in known VOFFSET state		
RESET_IRQZ	Z5	0				Active-low, output interrupt to ASIC		
		1	VOLTA	GE REGUL	ATOR MONITOR	RING		
PG_BIAS	E11	1				Active-low fault from external VBIAS regulator		
PG_OFFSET	B10	I			Pullup	Active-low fault from external VOFFSET regulator		
PG_RESET	D11	I				Active low from external VRESET regulator		
EN_BIAS	D9	0	LVCMOS			Active-high enable for external VBIAS regulator		
EN_OFFSET	C9	0				Active-high enable for external VOFFSET regulator		
EN_RESET	E9	0				Active-high enable for external VRESET regulator		



Table 5-1. Pin Functions (continued)							
	NO	TYPE ⁽⁵⁾	SIGNAL	DATA RATE ⁽²⁾	INTERNAL TERM ⁽³⁾	DESCRIPTION	TRACE (mils) ⁽⁴⁾
NAME	NO.		•				
MPDST(0)	C2	0	<u>L</u>	EAVE PIN (JNCONNECTED		
MBRST(0)		0			-		
MBRST(1)	C3				1		
MBRST(2)	C5 C4	0			-		
MBRST(3)					-		
MBRST(4)	E5	0			-		
MBRST(5)	E4	0			-		
MBRST(6)	E3	0			-	For proper DMD	
MBRST(7)	G4	0	Analog		Pulldown	operation, do not	
MBRST(8)	G3	0			4	connect.	
MBRST(9)	G2	0			_		
MBRST(10)	J4	0			-		
MBRST(11)	J3	0			1		
MBRST(12)	J2	0			1		
MBRST(13)	L4	0					
MBRST(14)	L3	0					
MBRST(15)	L2	0					
			L	EAVE PIN U	JNCONNECTED		
RESERVED_PFE	E7	I					
RESERVED_TM	D13	I	LVCMOS		Pulldown		
RESERVED_XI1	E13	I			For proper DMD operation, do not		
RESERVED_TP0	W12	I				connect.	
RESERVED_TP1	Y11	I	Analog				
RESERVED_TP2	X11	I					
			L	EAVE PIN U	JNCONNECTED		
RESERVED_BA	Y12	0				For proper DMD	
RESERVED_BB	C12	0	LVCMOS		1	operation, do not	
RESERVED_TS	D5	0			1	connect.	
		1	L	EAVE PIN U	JNCONNECTED	1	
NO CONNECT	B11						
NO CONNECT	C11				1		
NO CONNECT	C13				1	For proper DMD	
NO CONNECT	E12				1	operation, do not connect.	
NO CONNECT	E14				1		
NO CONNECT	E23				1		
NO CONNECT	H4						
NO CONNECT	N2				1		
NO CONNECT	N3				1		
NO CONNECT	N4				1	For proper DMD	
NO CONNECT	R2				1	operation, do not connect.	
NO CONNECT	R3				†	CONTINUE.	
NO CONNECT	R4				†		
NO CONNECT	T4				+		
	'7	1					



PIN ⁽¹⁾		TYPE ⁽⁵⁾	SIGNAL	DATA	INTERNAL	DESCRIPTION	TRACE (mils) ⁽⁴⁾
NAME	NO.	ITPE(*)	SIGNAL	RATE ⁽²⁾	TERM ⁽³⁾	DESCRIPTION	TRACE (IIIIS)
NO CONNECT	U2						
NO CONNECT	U3						
NO CONNECT	U4						
NO CONNECT	W3					For proper DMD	
NO CONNECT	W4					operation, do not	
NO CONNECT	W5					connect.	
NO CONNECT	W13						
NO CONNECT	W14						
NO CONNECT	W23						
NO CONNECT	X4						
NO CONNECT	X5						
NO CONNECT	X13						
NO CONNECT	Y2					For proper DMD	
NO CONNECT	Y3					operation, do not connect.	
NO CONNECT	Y4						
NO CONNECT	Y5						
NO CONNECT	Z11						

⁽¹⁾ The following power supplies are required to operate the DMD: VCC, VCCI, VOFFSET, VBIAS, and VRESET. VSS must also be connected.

⁽²⁾ DDR = Double Data Rate. SDR = Single Data Rate. Refer to Section 6.7 for specifications and relationships.

⁽³⁾ Internal term—CMOS level internal termination. Refer to Section 6.4 for differential termination specification.

⁽⁴⁾ Dielectric Constant for the DMD FYE package is approximately 9.6. For the package trace lengths shown: Propagation Speed = 11.8 / sqrt(9.6) = 3.808 in/ns. Propagation Delay = 0.262 ns/in = 262 ps/in = 10.315 ps/mm.

⁽⁵⁾ I = Input, O = Output, G = Ground



Table 5-2. Power Pin Functions

	PIN		i Fili FullCuolis	
NAME ⁽¹⁾	NO.	TYPE (I/O/P) ⁽²⁾	SIGNAL	DESCRIPTION
VBIAS	A6, A7, A8, AA6, AA7, AA8		Analog	Supply voltage for positive Bias level of micromirror reset signal
	A3, A4, A25		Analog	Supply voltage for HVCMOS logic
VOFFSET	B26, L26, M26		Analog	Supply voltage for stepped high voltage at micromirror address electrodes
	N26, Z26, AA3, AA4		Analog	Supply voltage for positive Offset level of micromirror reset signal
VRESET	G1, H1, J1, R1, T1, U1		Analog	Supply voltage for negative Reset level of micromirror reset signal
VCC	A9, B3, B5, B12, C1, C6, C10, D4, D6, D8, E1, E2, E10, E15, E16, E17, F3, H2, K1, K3, M4, P1, P3, T2, V3, W1, W2, W6, W9, W10, W15, W16, W17, X3, X6, Y1, Y8, Y13, Z1, Z3, Z12, AA2, AA9, AA10	-	Analog	Supply voltage for LVCMOS core logic. Supply voltage for normal high level at micromirror address electrodes. Supply voltage for positive Offset level of micromirror reset signal during power-down sequence
VCCI	A16, A17, A18, A20, A21, A23, AA16, AA17, AA18, AA20, AA21, AA23	Р	Analog	Supply voltage for LVDS receivers
VSS	A5, A10, A11, A19, A22, A24, B2, B4, B9, B13, B17, B20, B21, B24, C7, C15, C18, C21, C22, C26, D1, D3, D7, D10, D12, D14, D15, D16, D17, D18, D19, D20, D21, D22, D23, D26, E6, E8, E18, E19, E20, E21, E22, E26, F1, F2, F4, F23, F26, G23, G26, H3, H26, J26, K2, K4, K26, L1, M1, M2, M3, M23, M24, M25, N1, P2, P4, P26, R26, T3, T26, U23, U26, V1, V2, V4, V23, V26, W8, W18, W19, W20, W21, W22, W26, X1, X2, X7, X10, X12, X14, X15, X16, X17, X18, X19, X20, X21, X22, X23, X26, Y6, Y15, Y18, Y21, Y22, Y26, Z2, Z4, Z9, Z13, Z17, Z20, Z21, Z24, AA5, AA11, AA19, AA22, AA24		Analog	Device ground. Common return for all power

⁽¹⁾ The following power supplies are required to operate the DMD: VCC, VCCI, VOFFSET, VBIAS, and VRESET. VSS must also be connected.

⁽²⁾ P = Power



6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted). Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

		MIN	MAX	UNIT
SUPPLY VOLTAGES				
VCC	Supply voltage for LVCMOS core logic ⁽¹⁾	-0.5	4	V
VCCI	Supply voltage for LVDS receivers ⁽¹⁾	-0.5	4	V
VOFFSET	Supply voltage for HVCMOS and micromirror electrode ⁽¹⁾ (2)	-0.5	9	V
VBIAS	Supply voltage for micromirror electrode ⁽¹⁾	-0.5	17	V
VRESET	Supply voltage for micromirror electrode ⁽¹⁾	-11	0.5	V
VCC – VCCI	Supply voltage change (absolute value) ⁽³⁾		0.3	V
VBIAS – VOFFSET	Supply voltage change (absolute value) ⁽⁴⁾		8.75	V
INPUT VOLTAGES	,			
	Input voltage for all other LVCMOS input pins ⁽¹⁾	-0.5	VCC + 0.15	V
	Input voltage for all other LVDS input pins ^{(1) (5)}	-0.5	VCCI + 0.15	V
V _{ID}	Input differential voltage (absolute value) ⁽⁶⁾		700	mV
I _{ID}	Input differential current ⁽⁶⁾		7	mA
CLOCKS	,			
$f_{ m clock}$	Clock frequency for LVDS interface, DCLK (all channels)		460	MHz
ENVIRONMENTAL				
T	Temperature, operating ⁽⁷⁾	0	90	°C
T_{ARRAY} and T_{WINDOW}	Temperature: non-operating ⁽⁷⁾	-40	90	°C
T _{DELTA}	Absolute Temperature delta between any point on the window edge and the ceramic test point TP1 ⁽⁸⁾		30	°C
T _{DP}	Dew Point temperature, operating and non-operating (non-condensing)		81	°C

- (1) All voltages are referenced to common ground VSS. Supply voltages VCC, VCCI, VOFFSET, VBIAS, and VRESET are all required for proper DMD operation. VSS must also be connected.
- (2) VOFFSET supply transients must fall within specified voltages.
- (3) To prevent excess current, the supply voltage change |VCCI VCC| must be less than specified limit.
- (4) To prevent excess current, the supply voltage change |VBIAS VOFFSET| must be less than specified limit. Refer to Section 9 for additional information.
- (5) This maximum LVDS input voltage rating applies when each input of a differential pair is at the same voltage potential.
- (6) LVDS differential inputs must not exceed the specified limit or damage may result to the internal termination resistors
- (7) The highest temperature of the active array (as calculated by Section 7.6) or of any point along the Window Edge as defined in Figure 7-1. The locations of thermal test points TP2, TP3, TP4 and TP5 in Figure 7-1 are intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, add a test point to that location.
- (8) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 7-1. The window test points TP2, TP3, TP4, and TP5 in Figure 7-1 are intended to result in the worst-case delta. If a particular application causes another point on the window edge to result in a larger delta temperature, that point should be used.

6.2 Storage Conditions

Applicable for the DMD as a component or non-operational in a system.

		MIN	MAX	UNIT
T _{DMD}	DMD storage temperature	-40	80	°C
T _{DP-AVG}	Average dew point temperature (non-condensing) ⁽¹⁾		28	°C
T _{DP-ELR}	Elevated dew point temperature range (non-condensing) ⁽²⁾	28	36	°C

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6.2 Storage Conditions (continued)

Applicable for the DMD as a component or non-operational in a system.

		MIN	MAX	UNIT
CT _{ELR}	Cumulative time in elevated dew point temperature range		24	Months

The average over time (including storage and operating) that the device is not in the "elevated dew point temperature range."

6.3 ESD Ratings

				VALUE	UNIT
ſ	V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.4 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by this table. No level of performance is implied when operating the device above or below these limits.

		MIN	NOM	MAX	UNIT
SUPPLY VOLTAGES ⁽¹⁾ (2)	,				
VCC	Supply voltage for LVCMOS core logic	3.15	3.3	3.45	V
VCCI	Supply voltage for LVDS receivers	3.15	3.3	3.45	V
VOFFSET	Supply voltage for HVCMOS and micromirror electrodes ⁽²⁾	8.25	8.5	8.75	V
VBIAS	Supply voltage for micromirror electrodes	15.5	16	16.5	V
VRESET	Supply voltage for micromirror electrodes	-9.5	-10	-10.5	V
VCCI-VCC	Supply voltage change (absolute value) ⁽³⁾		0	0.3	V
VBIAS-VOFFSET	Supply voltage change (absolute value) ⁽⁴⁾			8.75	V
LVCMOS PINS					
V _{IH}	High level Input voltage ⁽⁵⁾	1.7	2.5	VCC + 0.15	V
V _{IL}	Low level Input voltage ⁽⁵⁾	-0.3		0.7	V
I _{OH}	High level output current at V _{OH} = 2.4 V			-20	mA
I _{OL}	Low level output current at V _{OL} = 0.4 V			15	mA
t _{PWRDNZ}	PWRDNZ pulse width ⁽⁶⁾	10			ns
SCP INTERFACE					
fscpclk	SCP clock frequency ⁽⁷⁾			500	kHz
t _{SCP_DS}	SCPDI clock setup time (before SCPCLK falling-edge) ⁽⁸⁾	800			ns
t _{SCP_DH}	SCPDI hold time (after SCPCLK falling-edge) ⁽⁸⁾	700			ns
t _{SCP_BYTE_INTERVAL}	Time between consecutive bytes	1			μs
t _{SCP_NEG_ENZ}	Time between falling edge of SCPENZ and the first rising edge of SCPCLK	30			ns
t _{SCP_PW_ENZ}	SCPENZ inactive pulse width (high level)	1			μs
t _{SCP_OUT_EN}	Time required for SCP output buffer to recover after SCPENZ (from tristate)			1.5	ns
f_{clock}	SCP circuit clock oscillator frequency (9)	9.6		11.1	MHz

Limit exposure to dew point temperatures in the elevated range during storage and operation to less than a total cumulative time of $\mathsf{CT}_{\mathsf{ELR}}.$



6.4 Recommended Operating Conditions (continued)

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by this table. No level of performance is implied when operating the device above or below these limits.

		MIN	NOM	MAX	UNIT
LVDS INTERFACE	<u> </u>				
$f_{ m clock}$	Clock frequency for LVDS interface, DCLK (all channels)		400	430	MHz
V _{ID}	Input differential voltage (absolute value) ⁽¹⁰⁾	200	400	600	mV
V_{CM}	Common mode ⁽¹⁰⁾		1200		mV
V _{LVDS}	LVDS voltage ⁽¹⁰⁾	0		2000	mV
t _{LVDS_RSTZ}	Time required for LVDS receivers to recover from PWRDNZ			10	ns
Z _{IN}	Internal differential termination resistance	95		105	Ω
Z _{LINE}	Line differential impedance (PWB/trace)	90	100	110	Ω
ENVIRONMENTAL					
T	Array temperature, long-term operational ⁽¹¹⁾ (12) (13) (14)	10		40 to 70 ⁽¹⁴⁾	°C
T _{ARRAY}	Array temperature, short-term operational 500-hr max ⁽¹²⁾ (15)	0		10	
T _{WINDOW}	Window temperature – operational ⁽¹⁶⁾			85	°C
T _{DELTA}	Absolute temperature delta between any point on the window edge and the ceramic test point TP1. (17)			15	°C
T _{DP-AVG}	Average dew point temperature (non-condensing) ⁽¹⁸⁾			28	°C
T _{DP-ELR}	Elevated dew point temperature range (non-condensing) ⁽¹⁹⁾	28		36	°C
CT _{ELR}	Cumulative time in elevated dew point temperature range			24	Months
LAMP					
ILL _{UV}	Illumination, wavelength < 395 nm ⁽¹¹⁾		0.68	2.0	mW/cm ²
ILL _{VIS}	Illumination, wavelength between 395 nm and 800 nm ⁽²⁰⁾			29.3	W/cm ²
ILL _{IR}	Illumination, wavelength > 800 nm			10	mW/cm ²
SOLID STATE					
ILL _{UV}	Illumination, wavelength < 410 nm ⁽¹¹⁾			0.45	mW/cm ²
ILL _{VIS}	Illumination, wavelength between 410 nm and 800 nm (20)			34.7	W/cm ²
ILL _{IR}	Illumination, wavelength > 800 nm			10	mW/cm ²

- (1) Supply voltages VCC, VCCI, VOFFSET, VBIAS, and VRESET are all required for proper DMD operation. VSS must also be connected.
- (2) VOFFSET supply transients must fall within specified max voltages.
- (3) To prevent excess current, the supply voltage change |VCCI VCC| must be less than specified limit.
- (4) To prevent excess current, the supply voltage change |VBIAS VOFFSET| must be less than specified limit. Refer to Section 9 for additional information.
- (5) Tester conditions for V_{IH} and V_{IL} :
 - Frequency = 60 MHz. Maximum Rise Time = 2.5 ns at (20% to 80%)
 - Frequency = 60 MHz. Maximum Fall Time = 2.5 ns at (80% to 20%)
- (6) PWRDNZ input pin resets the SCP and disables the LVDS receivers. PWRDNZ input pin overrides SCPENZ input pin and tristates the SCPDO output pin.
- (7) The SCP clock is a gated clock. Duty cycle shall be 50% ± 10%. SCP parameter is related to the frequency of DCLK.
- (8) Refer to Figure 6-2.
- (9) SCP internal oscillator is specified to operate all SCP registers. For all SCP operations, DCLK is required.
- (10) Refer to Figure 6-3, Figure 6-4, and Figure 6-5.
- (11) Simultaneous exposure of the DMD to the maximum Section 6.4 for temperature and UV illumination reduces device lifetime.
- (12) The array temperature cannot be measured directly and must be computed analytically from the temperature measured at test point 1 (TP1) shown in Figure 7-1 and the package thermal resistance using the calculation in Section 7.6.
- (13) Long-term is defined as the average over the usable life.
- (14) Per Figure 6-1, the maximum operational array temperature should be derated based on the micromirror landed duty cycle that the DMD experiences in the end application. See Section 7.7.
- (15) Short-term is the total cumulative time over the useful life of the device.
- (16) The locations of thermal test points TP2, TP3, TP4, and TP5 in Figure 7-1 are intended to measure the highest window edge temperature. For most applications, the locations shown are representative of the highest window edge temperature. If a particular application causes additional points on the window edge to be at a higher temperature, test points should be added to those locations.

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- (17) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 7-1. The window test points TP2, TP3, TP4, and TP5 shown in Figure 7-1 are intended to result in the worst-case delta temperature. If a particular application causes another point on the window edge to result in a larger delta in temperature, that point should be used.
- (18) The average over time (including storage and operating) that the device is not in the 'elevated dew point temperature range'.
- (19) Exposure to dew point temperatures in the elevated range during storage and operation should be limited to less than a total cumulative time of CT_{ELR}.
- (20) The maximum optical power that can be incident on the DMD is limited by the maximum optical power density and the micromirror array temperature.

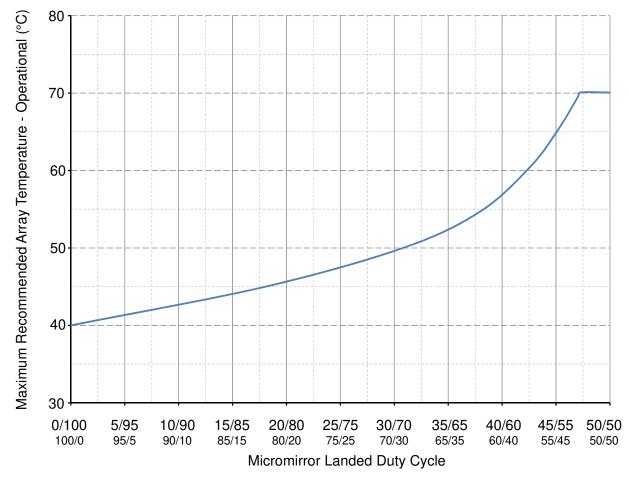


Figure 6-1. Recommended Maximum DMD Temperature—Derating Curve

6.5 Thermal Information

	DLP670RE	
THERMAL METRIC(1)		UNIT
	350 PINS	
Thermal resistance from active array to test point 1 (TP1)	0.50	°C/W

(1) The DMD is designed to conduct absorbed and dissipated heat to the back of the package where it can be removed by an appropriate heat sink. The heat sink and cooling system must be capable of maintaining the package within the temperature range specified in the *Recommended Operating Conditions*.

The total heat load on the DMD is largely driven by the incident light absorbed by the active area; although other contributions include light energy absorbed by the window aperture and electrical power dissipation of the array.

Optical systems should be designed to minimize the light energy falling outside the window clear aperture since any additional thermal load in this area can significantly degrade the reliability of the device.



6.6 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted).

	PARAMETER	TEST CONDITIONS ⁽¹⁾	MIN	TYP	MAX	UNIT	
V _{OH}	High-level output voltage	VCC = 3 V, I _{OH} = -20 mA	2.4			V	
V _{OL}	Low -level output voltage	VCC = 3.45 V, I _{OL} = 15 mA			0.4	V	
I _{IH}	High-level input current ^{(2) (3)}	VCC = 3.45 V, V _I = VCC			250	μA	
I _{IL}	Low-level input current	VCC = 3.45 V, V _I = 0	-250			μA	
l _{OZ}	High-impedance output current	VCC = 3.45 V			10	μA	
Icc	Supply support(4)	VCC = 3.45 V			1100	m 1	
I _{CC}	Supply current ⁽⁴⁾	VCCI = 3.45 V			510	510 mA	
I _{OFFSET}	Supply current ⁽⁵⁾ (6)	VOFFSET = 8.75 V		10	25	m Λ	
I _{BIAS}		VBIAS = 16.5 V		10	14	mA	
I _{RESET}	Complete summer (6)	VRESET = -10.5 V		10	11	Л	
I _{TOTAL}	Supply current ⁽⁶⁾	Total Sum			1650	mA	
Cı	Input capacitance	f = 1 MHz			20	pF	
Co	Output capacitance	f = 1 MHz			15	pF	
C _M	Reset group capacitance MBRST(14:0)	f = 1 MHz all inputs interconnected, (1920 x 1200) array	365		430	pF	

⁽¹⁾ All voltages are referenced to common ground VSS. Supply voltages VCC, VCCI, VOFFSET, VBIAS, and VRESET are all required for proper DMD operation. VSS must also be connected.

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⁽²⁾ Applies to LVCMOS input pins only; excludes LVDS pins and MBRST pins.

⁽³⁾ LVCMOS input pins utilize an internal 18000-Ω passive resistor for pullup and pulldown configurations. Refer to Section 5 to determine pullup or pulldown configuration used.

⁽⁴⁾ To prevent excess current, the supply voltage change |VCCI - VCC| must be less than specified limit.

⁽⁵⁾ To prevent excess current, the supply voltage change |VBIAS – VOFFSET| must be less than specified limit.

⁽⁶⁾ The DLPA4000 PMIC is able to supply enough current to the VOFFSET, VBIAS, and VRESET pins to correctly operate the DLP670RE.



6.7 Timing Requirements

Over Recommended Operating Conditions (Section 6.4) unless otherwise noted. (5)

	·	DESC	CRIPTION ⁽¹⁾	MIN	TYP	MAX	UNIT
SCP IN	TERFACE ⁽²⁾			•			
t _r	Rise time	20% to 80% reference po	pints			200	ns
t_f	Fall time	80% to 20% reference po	pints			200	ns
LVDS II	NTERFACE ⁽²⁾						
t _r	Rise time	20% to 80%		100		400	ps
t_f	Fall time	80% to 20%		100		400	ps
LVDS C	CLOCKS(3)	<u>'</u>					
	Cuala tima	DCLK_A, 50% to 50%		2.5			
t _c	Cycle time	DCLK_B, 50% to 50%		2.5			ns
	B	DCLK_A, 50% to 50%		1.19	1.25		
t _w	Pulse duration	DCLK_B, 50% to 50%		1.19	1.25		ns
LVDS II	NTERFACE ⁽³⁾				,		
	O the time time to	D_A(15:0) before rising o	r falling edge of DCLK_A	0.17			
t _{su}	Setup time	D_B(15:0) before rising o	ore rising or falling edge of DCLK_B				ns
	0.1. "	SCTRL_A before rising o	r falling edge of DCLK_A	0.17			
t _{su} Setup time		SCTRL_B before rising o	SCTRL_B before rising or falling edge of DCLK_B				ns
	Hald Bara	D_A(15:0) after rising or falling edge of DCLK_A		0.47			
t _h	Hold time	D_B(15:0) after rising or f	falling edge of DCLK_B	0.47			ns
	11.116	SCTRL_A after rising or f	alling edge of DCLK_A	0.47			
t _h	Hold time	SCTRL_B after rising or f	alling edge of DCLK_B	0.47	,		ns
LVDS II	NTERFACE ⁽⁴⁾						
t _{skew}	Skew time	Channel B relative to Channel A ⁽⁴⁾	Channel A includes the following LVDS pairs: DCLK_AP and DCLK_AN SCTRL_AP and SCTRL_AN D_AP(15:0) and D_AN(15:0) Channel B includes the	-1.25		1.25	ns
	Cr	Shamor A.	following LVDS pairs: DCLK_BP and DCLK_BN SCTRL_BP and SCTRL_BN D_BP(15:0) and D_BN(15:0)				

Refer to Section 5 for pin details.

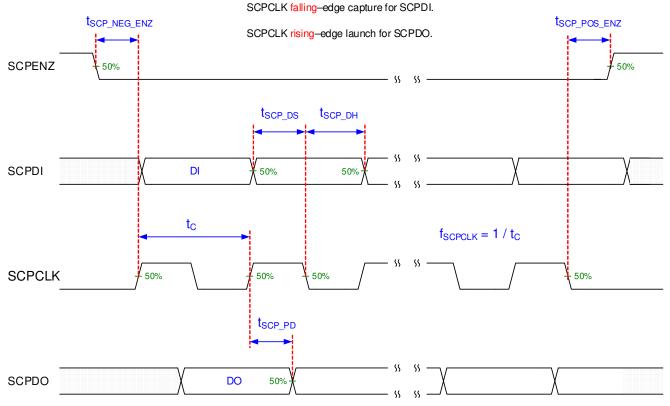
⁽²⁾ (3) (4) Refer to Figure 6-6.

Refer to Figure 6-8.

Refer to Figure 6-9.

Tested at the device pin. For output timing analysis, the tester pin electronics and its transmission line effects must be considered.





Not to scale

Refer to the SCP Interface section of the Recommended Operating Conditions Section 6.4.

V_{IP} + V_{IN}) / 2

DCLK_P, SCTRL_P, D_P(0:?)

LVDS
Receiver

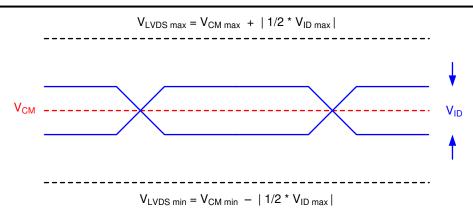
V_{IN}

V_{IN}

Figure 6-2. SCP Timing Parameters

Refer to the LVDS Interface section of the *Recommended Operating Conditions* (Section 6.4). Refer to the Pin Functions table for the list of LVDS pins.

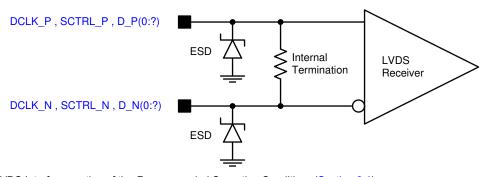
Figure 6-3. LVDS Voltage Definitions (References)



Not to scale

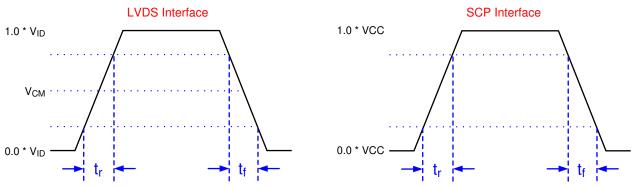
Refer to the LVDS Interface section of the Recommended Operating Conditions (Section 6.4).

Figure 6-4. LVDS Voltage Parameters



Refer to the LVDS Interface section of the *Recommended Operating Conditions* (Section 6.4). Refer to the Pin Functions table for the list of LVDS pins.

Figure 6-5. LVDS Equivalent Input Circuit



Not to scale

Refer to the timing requirements.

Refer to the Pin Functions table for the list of LVDS pins and SCP pins.

Figure 6-6. Rise Time and Fall Time



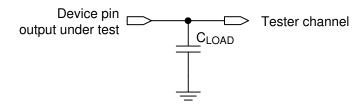
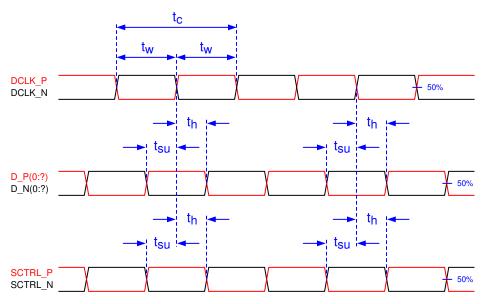


Figure 6-7. Test Load Circuit for Output Propagation Measurement

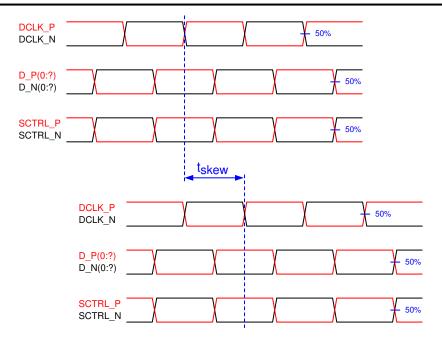
For output timing analysis, the tester pin electronics and its transmission line effects must be considered. System design should use IBIS or other simulation tools to correlate the timing reference load to a system environment. See Figure 6-7.



Not to scale

Refer to the LVDS Interface section in the timing requirements.

Figure 6-8. Timing Requirement Parameter Definitions



Not to scale

Refer to the LVDS Interface section in the timing requirements.

Figure 6-9. LVDS Interface Channel Skew Definition

6.8 System Mounting Interface Loads

PARAMETER	MIN	NOM	MAX	UNIT
Maximum load to be applied to the electrical interface area ⁽¹⁾			111	N
Maximum load to be applied to the thermal interface area ⁽¹⁾			111	N

(1) The load must be uniformly applied in the corresponding areas shown in Figure 6-10.

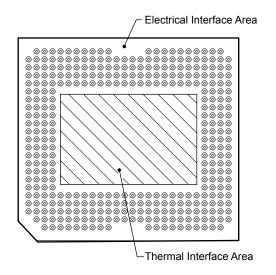


Figure 6-10. System Mounting Interface Loads

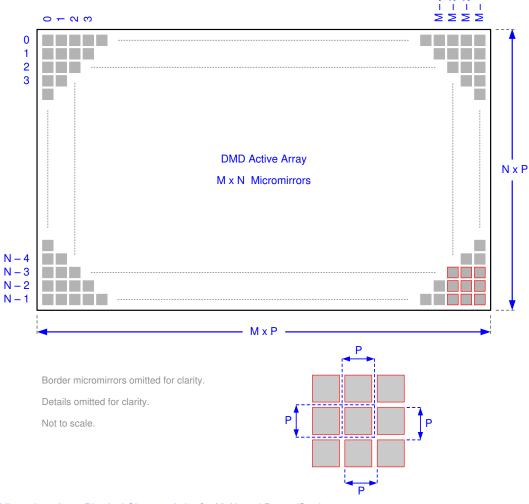


6.9 Micromirror Array Physical Characteristics

		VALUE	UNIT
Number of active columns ⁽¹⁾	M	1920	micromirrors
Number of active rows ⁽¹⁾	N	1200	micromirrors
Micromirror (pixel) pitch ⁽¹⁾	Р	7.56	μm
Micromirror active array width ⁽¹⁾	Micromirror Pitch × number of active columns	14.5152	mm
Micromirror active array height ⁽¹⁾	Micromirror Pitch × number of active rows	9.072	mm
Micromirror active border ⁽²⁾	Pond of micromirrors (POM)	14	micromirrors /side

⁽¹⁾ See Figure 6-11.

⁽²⁾ The structure and qualities of the border around the active array includes a band of partially functional micromirrors referred to as the pond of micromirrors (POM). These micromirrors are structurally and/or electrically prevented from tilting toward the bright or ON state, but still require an electrical bias to tilt toward OFF.



Refer to Micromirror Array Physical Characteristics for M, N, and P specifications.

Figure 6-11. Micromirror Array Physical Characteristics

6.10 Micromirror Array Optical Characteristics

See Section 7.5 for important information.

PARAMETER	MIN	NOM	MAX	UNIT
Mirror tilt angle, variation device to device ⁽¹⁾ (2) (3) (4)	11	12	13	o

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6.10 Micromirror Array Optical Characteristics (continued)

See Section 7.5 for important information.

PARA	METER		MIN	NOM	MAX	UNIT
Micromirror crossover time ⁽⁵⁾				2.5		μm
Micromirror switching time ⁽⁶⁾			10			μm
	Bright pixels(s) in active area ⁽⁸⁾	Gray 10 Screen ⁽⁹⁾			0	micromirrors
Image performance ⁽⁷⁾	Bright pixels(s) in POM ⁽¹⁰⁾	Gray 10 Screen ⁽⁹⁾			1	micromirrors
imago periormanos	Dark pixel(s) in active area ⁽¹¹⁾	White Screen			4	micromirrors
	Adjacent pixels ⁽¹²⁾	Any Screen			0	micromirrors
	Unstable pixel(s) in active area ⁽¹³⁾	Any Screen			0	micromirrors

- (1) Measured relative to the plane formed by the overall micromirror array.
- (2) Represents the variation that can occur between any two individual micromirrors, located on the same device or located on different devices.
- (3) For some applications, it is critical to account for the micromirror tilt angle variation in the overall system optical design. With some system optical designs, the micromirror tilt angle variation within a device may result in perceivable non-uniformities in the light field reflected from the micromirror array. With some system optical designs, the micromirror tilt angle variation between devices may result in colorimetry variations, system efficiency variations or system contrast variations.
- (4) When the micromirror array is landed (not parked), the tilt direction of each individual micromirror is dictated by the binary contents of the CMOS memory cell associated with each individual micromirror. A binary value of 1 results in a micromirror landing in the ON State direction. A binary value of 0 results in a micromirror landing in the OFF State direction, see Figure 6-12.
- (5) The time required for a micromirror to nominally transition from one landed state to the opposite landed state.
- (6) The minimum time between successive transitions of a micromirror.
- (7) Conditions of Acceptance: All DMD image performance returns will be evaluated using the following projected image test conditions:

Test set degamma shall be linear

Test set brightness and contrast shall be set to nominal

The diagonal size of the projected image shall be a minimum of 60 inches

The projection screen shall be 1x gain

The projected image shall be inspected from an 8-foot minimum viewing distance

The image shall be in focus during all image performance tests

- (8) Bright pixel definition: A single pixel or mirror that is stuck in the ON position and is visibly brighter that the surrounding pixels
- (9) Gray 10 screen definition: All areas of the screen are colored with the following settings:

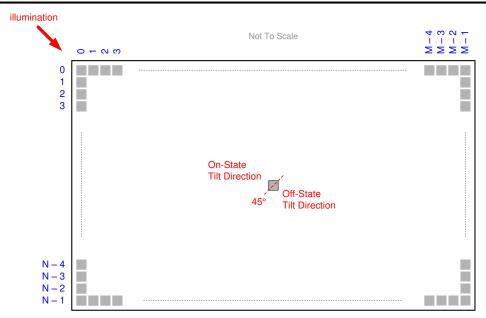
Red = 10/255

Green = 10/255

Blue = 10/255

- (10) POM definition: Rectangular border of off-state mirror surrounding the active area.
- (11) Dark pixel definition: A single pixel or mirror that is stuck in the OFF position and is visibly darker than the surrounding pixels.
- (12) Adjacent pixel definition: Two or more stuck pixels sharing a common border or common point, also referred to as a cluster.
- (13) Unstable pixel definition: A single pixel or mirror that does not operate in sequence with the parameters loaded into memory. The unstable pixel appears to be flickering asynchronously with the image.





Refer to Micromirror Array Physical Characteristics for M, N, and P specifications.

Figure 6-12. Micromirror Landed Orientation and Tilt

6.11 Window Characteristics

PARAMETER	MIN	NOM
Window material		Corning Eagle XG
Window refractive index at wavelength 546.1 nm		1.5119
Window Transmittance, minimum within the wavelength range 420–680 nm. Applies to all angles 0–30° AOI. ⁽¹⁾ (2)	97%	
Window Transmittance, average over the wavelength range 420–680 nm. Applies to all angles 30–45° AOI. ⁽¹⁾ (2)	97%	

- (1) Single-pass through both surfaces and glass
- (2) Angle of incidence (AOI) is the angle between an incident ray and the normal to a reflecting or refracting surface.

6.12 Chipset Component Usage Specification

The DLP670RE is a component of one or more DLP chipsets. Reliable function and operation of the DLP670RE require that it is used in conjunction with the other components of the applicable DLP chipset, including those components that contain or implement TI DMD control technology. TI DMD control technology is the TI technology and devices for operating or controlling a DLP DMD.

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7 Detailed Description

7.1 Overview

DLP670RE is a 0.67-inch diagonal spatial light modulator which consists of an array of highly reflective aluminum micromirrors. Pixel array size and square grid pixel arrangement are shown in Figure 6-11.

The DMD is an electrical input, optical output micro-electrical-mechanical system (MEMS). The electrical interface is low voltage differential signaling (LVDS), double data rate (DDR).

DLP670RE DMD consists of a two-dimensional array of 1-bit CMOS memory cells. The array is organized in a grid of *M* memory cell columns by *N* memory cell rows. Refer to the Functional Block Diagram.

The positive or negative deflection angle of the micromirrors can be individually controlled by changing the address voltage of underlying CMOS addressing circuitry and micromirror reset signals (MBRST).

Each cell of the $M \times N$ memory array drives its true and complement ('Q' and 'QB') data to two electrodes underlying one micromirror, one electrode on each side of the diagonal axis of rotation. Refer to Section 6.10. The micromirrors are electrically tied to the micromirror reset signals (MBRST) and the micromirror array is divided into reset groups.

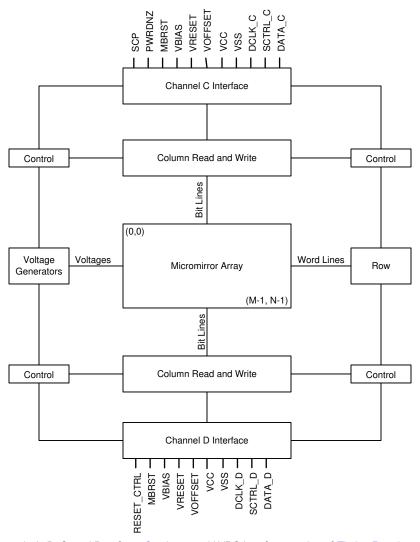
Electrostatic potentials between a micromirror and its memory data electrodes cause the micromirror to tilt toward the illumination source in a DLP projection system or away from it, thus reflecting its incident light into or out of an optical collection aperture. The positive (+) tilt angle state corresponds to an 'on' pixel, and the negative (–) tilt angle state corresponds to an 'off' pixel.

Refer to *Micromirror Array Optical Characteristics* for the ± tilt angle specifications. Refer to Section 5 for more information on micromirror reset control.



7.2 Functional Block Diagram

The main LVDS lines going to the DMD are connected via channel A and B. However, the LVDS lines come from channel C and D off the DLPC4430. Refer to the *DLPC4430 Display Controller DataSheet* for more information.



For pin details on Channels A, B, C, and D, refer to Section 5 and LVDS Interface section of *Timing Requirements*.

7.3 Feature Description

7.3.1 Power Interface

The DMD requires four DC voltage input signals.

- DMD P3P3V
- VOFFSET
- VRESET
- VBIAS

The DMD_P3P3V signal is created by the power and motor driver of the DLPA100 device. It is used on the DMD board to create the other three DMD voltage inputs, as well as powering various peripherals (for example, TMP411, I²C, and TI level translators). The other signals (VOFFSET (8.5 V), VRESET (–10 V), and VBIAS(16.5 V)) are created by the TI PMIC TPS65145 device and are supplied to the DMD to control the micromirrors.



7.3.2 Timing

The data sheet provides a timing analysis as measured at the device pin. For an output timing analysis, the tester pin electronics and its transmission line effects must be considered. Figure 6-7 shows an equivalent test load circuit for the output under test. Timing reference loads are not intended as a precise representation of any particular system environment or depiction of the actual load presented by a production test. TI suggests that system designers use IBIS or other simulation tools to correlate the timing reference load to a system environment. The load capacitance value stated is only for characterization and measurement of AC timing signals. This load capacitance value does not indicate the maximum load the device is capable of driving.

7.4 Device Functional Modes

DMD functional modes are controlled by the DLPC4430 digital display controller. See the *DLPC4430 DLP® Display Controller Data Sheet*. Contact a TI applications engineer for more information.

7.5 Optical Interface and System Image Quality Considerations

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. System optical performance and image quality strongly relate to optical system design parameter trades offs. Although it is not possible to anticipate every conceivable application, projector image quality and optical performance is contingent on compliance to the optical system operating conditions described in the following sections.

7.5.1 Numerical Aperture and Stray Light Control

The angle defined by the numerical aperture of the illumination and projection optics at the DMD optical area are the same. This angle should not exceed the nominal device mirror tilt angle unless appropriate apertures are added in the illumination and/or projection pupils to block out flat-state and stray light from the projection lens. The micromirror tilt angle defines DMD capability to separate the "ON" optical path from any other light path, including undesirable flat-state specular reflections from the DMD window, DMD border structures, or other system surfaces near the DMD such as prism or lens surfaces. If the numerical aperture exceeds the mirror tilt angle, or if the projection numerical aperture angle is more than two degrees larger than the illumination numerical aperture angle (and vice versa), objectionable artifacts in the display's border and/or active area could occur.

7.5.2 Pupil Match

TI's optical and image quality specifications assume that the exit pupil of the illumination optics is nominally centered within 2° of the entrance pupil of the projection optics. Misalignment of pupils can create objectionable artifacts in the display's border and/or active area, which may require additional system apertures to control, especially if the numerical aperture of the system exceeds the pixel tilt angle.

7.5.3 Illumination Overfill

The active area of the device is surrounded by an aperture on the inside DMD window surface that masks structures of the DMD chip assembly from normal view. The aperture is sized to anticipate several optical operating conditions. Overfill light illuminating the window aperture can create artifacts from the edge of the window aperture opening and other surface anomalies that may be visible on the screen. Design the illumination optical system to limit light flux incident anywhere on the window aperture from exceeding approximately 10% of the average flux level in the active area. Depending on the particular system's optical architecture, overfill light may have to be further reduced below the suggested 10% level in order to be acceptable.



7.6 Micromirror Array Temperature Calculation

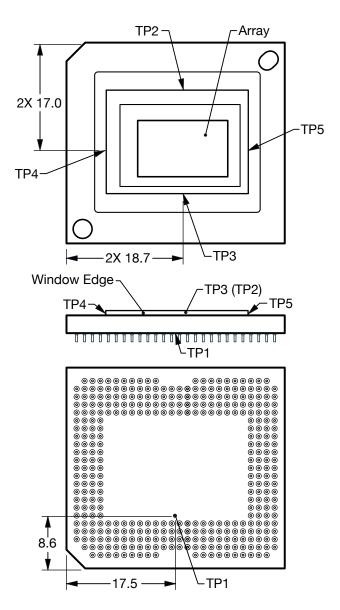


Figure 7-1. DMD Thermal Test Points

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Micromirror array temperature cannot be measured directly, therefore it must be computed analytically from measurement points on the outside of the package, the package thermal resistance, the electrical power, and the illumination heat load. The relationship between array temperature and the reference ceramic temperature (thermal test TP1 in Figure 7-1) is provided by the following equations:

$$T_{ARRAY} = T_{CERAMIC} + (Q_{ARRAY} \times R_{ARRAY-TO-CERAMIC})$$
 (1)

$$Q_{ARRAY} = Q_{ELECTRICAL} + Q_{ILLUMINATION}$$
 (2)

where

- T_{ARRAY} = Computed array temperature (°C)
- T_{CERAMIC} = Measured ceramic temperature (°C) (TP1 location)
- R_{ARRAY-TO-CERAMIC} = Thermal resistance of package specified in *Thermal Information* from array to ceramic TP1 (°C/Watt)
- Q_{ARRAY} = Total DMD power on the array (W) (electrical + absorbed)
- Q_{ELECTRICAL} = Nominal electrical power (W)
- Q_{INCIDENT} = Incident illumination optical power (W)
- Q_{ILLUMINATION} = (DMD average thermal absorptivity × Q_{INCIDENT}) (W)
- DMD average thermal absorptivity = 0.42

The electrical power dissipation of the DMD is variable and depends on the voltages, data rates, and operating frequencies. A nominal electrical power dissipation to use when calculating array temperature is 3.0 W. The absorbed power from the illumination source is variable and depends on the operating state of the micromirrors and the intensity of the light source. The equations shown above are valid for a single chip or multichip DMD system. It assumes an illumination distribution of 83.7% on the active array, and 16.3% on the array border.

The sample calculation for a typical projection application is as follows:

$$Q_{INCIDENT} = 25 \text{ W (measured)}$$
 (3)

$$T_{CERAMIC} = 55.0^{\circ}C \text{ (measured)}$$
 (4)

$$Q_{ELECTRICAL} = 3.0 \text{ W}$$
 (5)

$$Q_{ARRAY} = 3.0 \text{ W} + (0.42 \times 25 \text{ W}) = 13.5 \text{ W}$$
 (6)

$$T_{ARRAY} = 55.0^{\circ}C + (13.5 \text{ W} \times 0.5^{\circ}C/\text{W}) = 61.8^{\circ}C$$
 (7)

7.7 Micromirror Landed-On or Landed-Off Duty Cycle

7.7.1 Definition of Micromirror Landed-On or Landed-Off Duty Cycle

The micromirror landed-on or landed-off duty cycle (landed duty cycle) denotes the amount of time (as a percentage) that an individual micromirror is landed in the ON–state versus the amount of time the same micromirror is landed in the OFF–state.

As an example, a landed duty cycle of 100/0 indicates that the referenced pixel is in the ON–state 100% of the time (and in the OFF–state 0% of the time); whereas 0/100 would indicate that the pixel is in the OFF–state 100% of the time. Likewise, 50/50 indicates that the pixel is On 50% of the time and Off 50% of the time.

Note that when assessing landed duty cycle, the time spent switching from one state (ON or OFF) to the other state (OFF or ON) is considered negligible and is thus ignored.

Since a micromirror can only be landed in one state or the other (ON or OFF), the two numbers (percentages) always add to 100.



7.7.2 Landed Duty Cycle and Useful Life of the DMD

Knowing the long-term average landed duty cycle (of the end product or application) is important because subjecting all (or a portion) of the DMD's micromirror array (also called the active array) to an asymmetric landed duty cycle for a prolonged period of time can reduce the DMD's usable life.

Note that it is the symmetry/asymmetry of the landed duty cycle that is of relevance. The symmetry of the landed duty cycle is determined by how close the two numbers (percentages) are to being equal. For example, a landed duty cycle of 50/50 is perfectly symmetrical whereas a landed duty cycle of 100/0 or 0/100 is perfectly asymmetrical.

Individual DMD mirror duty cycles vary by application as well as the mirror location on the DMD within any specific application. DMD mirror useful life are maximized when every individual mirror within a DMD approaches 50/50 (or 1/1) duty cycle. Examples are whenever the system goes to standby, the illumination is disabled, between sequential pattern exposures (if possible), or when the exposure pattern sequence is stopped for any reason. This software mode provides a 50/50 duty cycle across the entire DMD mirror array at power down, where the mirrors are continuously flipped between the ON and OFF states.

7.7.3 Landed Duty Cycle and Operational DMD Temperature

Operational DMD Temperature and Landed Duty Cycle interact to affect the DMD usable life, and this interaction can be exploited to reduce the impact that an asymmetrical Landed Duty Cycle has on the usable life of the DMD. This is quantified in the de-rating curve shown in Figure 6-1. The importance of this curve is that:

- · All points along this curve represent the same usable life.
- All points above this curve represent lower usable life (and the further away from the curve, the lower the usable life).
- All points below this curve represent higher usable life (and the further away from the curve, the higher the usable life).

In practice, this curve specifies the maximum operating DMD temperature at a given long-term average Landed Duty Cycle.

7.7.4 Estimating the Long-Term Average Landed Duty Cycle of a Product or Application

During a given time period, the Landed Duty Cycle of a given pixel follows from the image content being displayed by that pixel.

For example, in the simplest case, when displaying pure-white on a given pixel for a given time period, that pixel operates under a 100/0 Landed Duty Cycle during that time period. Likewise, when displaying pure-black, the pixel operates under a 0/100 Landed Duty Cycle.

Between the two extremes (ignoring for the moment color and any image processing that may be applied to an incoming image), the Landed Duty Cycle tracks one-to-one with the gray scale value, as shown in Table 7-1.

Table 7-1. Grayscale Value and Landed Duty Cycle

GRAYSCALE VALUE	LANDED DUTY CYCLE
0%	0/100
10%	10/90
20%	20/80
30%	30/70
40%	40/60
50%	50/50
60%	60/40
70%	70/30
80%	80/20
90%	90/10
100%	100/0

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Accounting for color rendition (but still ignoring image processing) requires knowing both the color intensity (from 0% to 100%) for each constituent primary color (red, green, and/or blue) for the given pixel as well as the color cycle time for each primary color, where color cycle time is the total percentage of the frame time that a given primary must be displayed in order to achieve the desired white point.

During a given period of time, the landed duty cycle of a given pixel can be calculated in Equation 8.

Landed Duty Cycle = (Red_Cycle_% × Red_Scale_Value) + (Green_Cycle_% × Green_Scale_Value) + (Blue_Cycle_% (8) × Blue Scale Value)

where

- Red Cycle % represents the percentage of the frame time that Red is displayed to achieve the desired white point
- Green Cycle % represents the percentage of the frame time that Green is displayed to achieve the desired white point
- Blue Cycle %, represents the percentage of the frame time that Blue is displayed to achieve the desired white point

For example, assume that the red, green and blue color cycle times are 50%, 20%, and 30% respectively (in order to achieve the desired white point), then the Landed Duty Cycle for various combinations of red, green, blue color intensities would be as shown in Table 7-2.

Table 7-2. Example Landed Duty Cycle for Full-Color

	CYCLE PERCENTAGE					
Red 50%	Green 20%	Blue 30%	Landed Duty Cycle 0/100			
Red Scale Value	Green Scale Value	Blue Scale Value				
0%	0%	0%				
100%	0%	0%	50/50			
0%	100%	0%	20/80			
0%	0%	100%	30/70			
12%	0%	0%	6/94			
0%	35%	0%	7/93			
0%	0%	60%	18/82			
100%	100%	0%	70/30			
0%	100%	100%	50/50			
100%	0%	100%	80/20			
12%	35%	0%	13/87			
0%	35%	60%	25/75			
12%	0%	60%	24/76			
100%	100%	100%	100/0			



8 Application and Implementation

Note

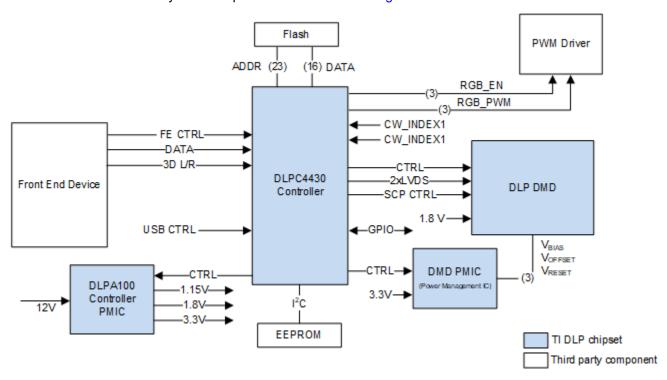
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

Texas Instruments DLP technology is a micro-electro-mechanical systems (MEMS) technology that modulates light using a digital micromirror device (DMD). The DMD is a spatial light modulator, which reflects incoming light from an illumination source to one of two directions, towards the projection optics or collection optics. The large micromirror array size and ceramic package provides great thermal performance for bright display applications. Typical applications using the DLP670RE include home theater, digital signage, interactive display, low-latency gaming display, portable smart displays.

8.2 Typical Application

The DLP670RE DMD combined with a DLPC4430 digital controller and DLPA100 power management device provides WUXGA resolution for bright, colorful display applications. A typical display system using the DLP670RE and additional system components can be seen in Figure 8-1.





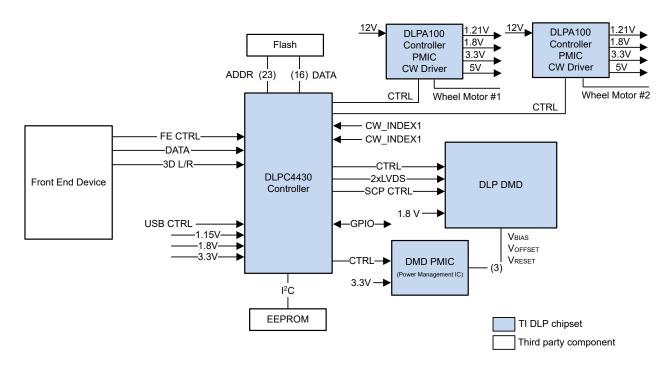


Figure 8-1. Typical DLPC4430 Application (LED - top, LPCW - bottom)

8.2.1 Design Requirements

A DLP670RE projection system is created by using the DMD chipset, including the DLP670RE, DLPC4430, and DLPA100. The DLP670RE is used as the core imaging device in the display system and contains a 0.67-inch array of micromirrors. The DLPC4430 controller is the digital interface between the DMD and the rest of the system, taking digital input from front end receiver that converts the data from the source and using the converted data for driving the DMD over a LVDS interface. The DLPA100 power management device provides voltage regulators for the DMD, controller, and illumination functionality.

Other core components of the display system include an illumination source, an optical engine for the illumination and projection optics, other electrical and mechanical components, and software. The illumination source options include lamp, LED, laser or laser phosphor. The type of illumination used and desired brightness affects the overall system design and size.

8.2.2 Detailed Design Procedure

For a complete DLP system, an optical module or light engine is required that contains the DLP670RE DMD, associated illumination sources, optical elements, and necessary mechanical components.

To ensure reliable operation, the DLP670RE DMD must always be used with the DLPC4430 display controllers and a DLPA100 PMIC driver.



9 Power Supply Requirements

9.1 DMD Power Supply Requirements

The following power supplies are all required to operate the DMD: VCC, VCCI, VOFFSET, VBIAS, and VRESET. VSS must also be connected. DMD power-up and power-down sequencing is strictly controlled by the DLPC4430 device.

CAUTION

For reliable operation of the DMD, the following power supply sequencing requirements must be followed. Failure to adhere to the prescribed power-up and power-down procedures may affect device reliability. VCC, VCCI, VOFFSET, VBIAS, and VRESET power supplies have to be coordinated during power-up and power-down operations. VSS must also be connected. Failure to meet any of the below requirements results in a significant reduction in the DMD's reliability and lifetime. Refer to Figure 9-1.

9.2 DMD Power Supply Power-Up Procedure

- During power-up, VCC and VCCI must always start and settle before VOFFSET, VBIAS, and VRESET voltages are applied to the DMD.
- During power-up, it is a strict requirement that the change between VBIAS and VOFFSET must be within the specified limit shown in *Recommended Operating Conditions*. During power-up, VBIAS does not have to start after VOFFSET.
- During power-up, there is no requirement for the relative timing of VRESET with respect to VOFFSET and VBIAS.
- Power supply slew rates during power-up are flexible, provided that the transient voltage levels follow the requirements listed in the *Absolute Maximum Ratings* table, in the *Recommended Operating Conditions* table, and in the *DMD Power Supply Sequencing Requirements* section.
- During power-up, LVCMOS input pins must not be driven high until after VCC and VCCI have settled at operating voltages listed in the Recommended Operating Conditions table.

9.3 DMD Power Supply Power-Down Procedure

- During power-down, VCC and VCCI must be supplied until after VBIAS, VRESET, and VOFFSET are discharged to within the specified limit of ground. Refer to Table 9-1.
- During power-down, it is a strict requirement that the change between VBIAS and VOFFSET must be within
 the specified limit shown in the *Recommended Operating Conditions* table. During power-down, it is not
 mandatory to stop driving VBIAS prior to VOFFSET.
- During power-down, there is no requirement for the relative timing of VRESET with respect to VOFFSET and VBIAS.
- Power supply slew rates during power-down are flexible, provided that the transient voltage levels follow the requirements listed in *Absolute Maximum Ratings*, in *Recommended Operating Conditions*, and in Figure 9-1.
- During power-down, LVCMOS input pins must be less than specified in the Recommended Operating Conditions table.

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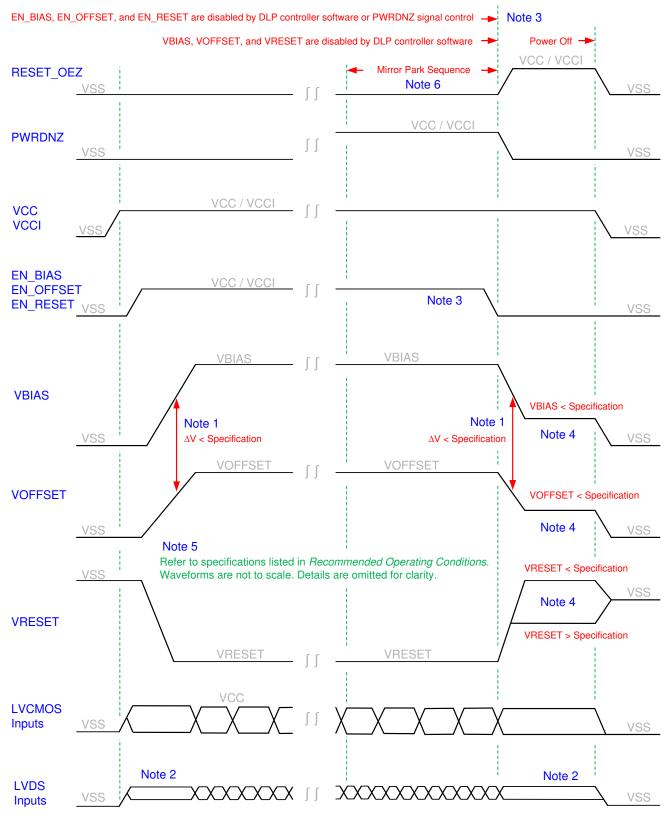


Figure 9-1. DMD Power Supply Sequencing Requirements

To prevent excess current, the supply voltage change |VBIAS - VOFFSET| must be less than specified in the Recommended Operating Conditions table. OEMs may find that the most reliable way to ensure this is to power VOFFSET prior to VBIAS during power-up and to remove VBIAS prior to VOFFSET during power-down.



- B. LVDS signals are less than the input differential voltage (VID) maximum specified in the *Recommended Operating Conditions* table.

 During power-down, LVDS signals are less than the high level input voltage (VIH) maximum specified in the *Recommended Operating Conditions* table.
- C. When system power is interrupted, the DLP DLPC4430 initiates a hardware power-down that activates PWRDNZ and disables VBIAS, VRESET and VOFFSET after the micromirror park sequence. Software power-down disables VBIAS, VRESET, and VOFFSET after the micromirror park sequence through software control. For either case, enable signals EN_BIAS, EN_OFFSET, and EN_RESET are used to disable VBIAS, VOFFSET, and VRESET, respectfully.
- D. Refer to Table 9-1.
- E. Figure not to scale. Details have been omitted for clarity. Refer to the Recommended Operating Conditions table.
- F. EN_BIAS, EN_OFFSET, and EN_RESET are disabled by DLP controller software or PWRDNZ signal control.
- G. VBIAS, VOFFSET, and VRESET are disabled by DLP controller software

Table 9-1. DMD Power-Down Sequence Requirements

	MIN	MAX	UNIT	
VBIAS			4.0	V
VOFFSET	Supply voltage level during power–down sequence		4.0	V
VRESET		-4.0	0.5	V

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10 Device Documentation Support

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10.2 Device Support

10.2.1 Device Nomenclature

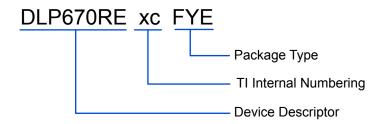


Figure 10-1. Device Number Description

10.2.2 Device Markings

The device marking will include both human-readable information and a 2-dimensional matrix code. The human-readable information is described in Figure 10-2. The 2-dimensional matrix code is an alpha-numeric character string that contains the DMD part number, Part 1, and Part 2 of Serial Number.

Example:

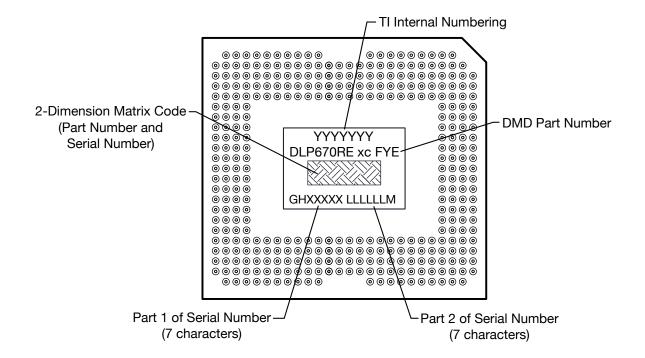


Figure 10-2. DMD Marking



10.3 Documentation Support

10.3.1 Related Documentation

The following documents contain additional information related to the use of the DLP670RE device.

- TPS65145 Triple output LCD Supply With Linear Regulator and Power Good
- DLPA100 Power Management and Motor Driver
- DMD101: Introduction to Digital Micromirror Device (DMD) Technology

10.4 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.5 Support Resources

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10.7 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

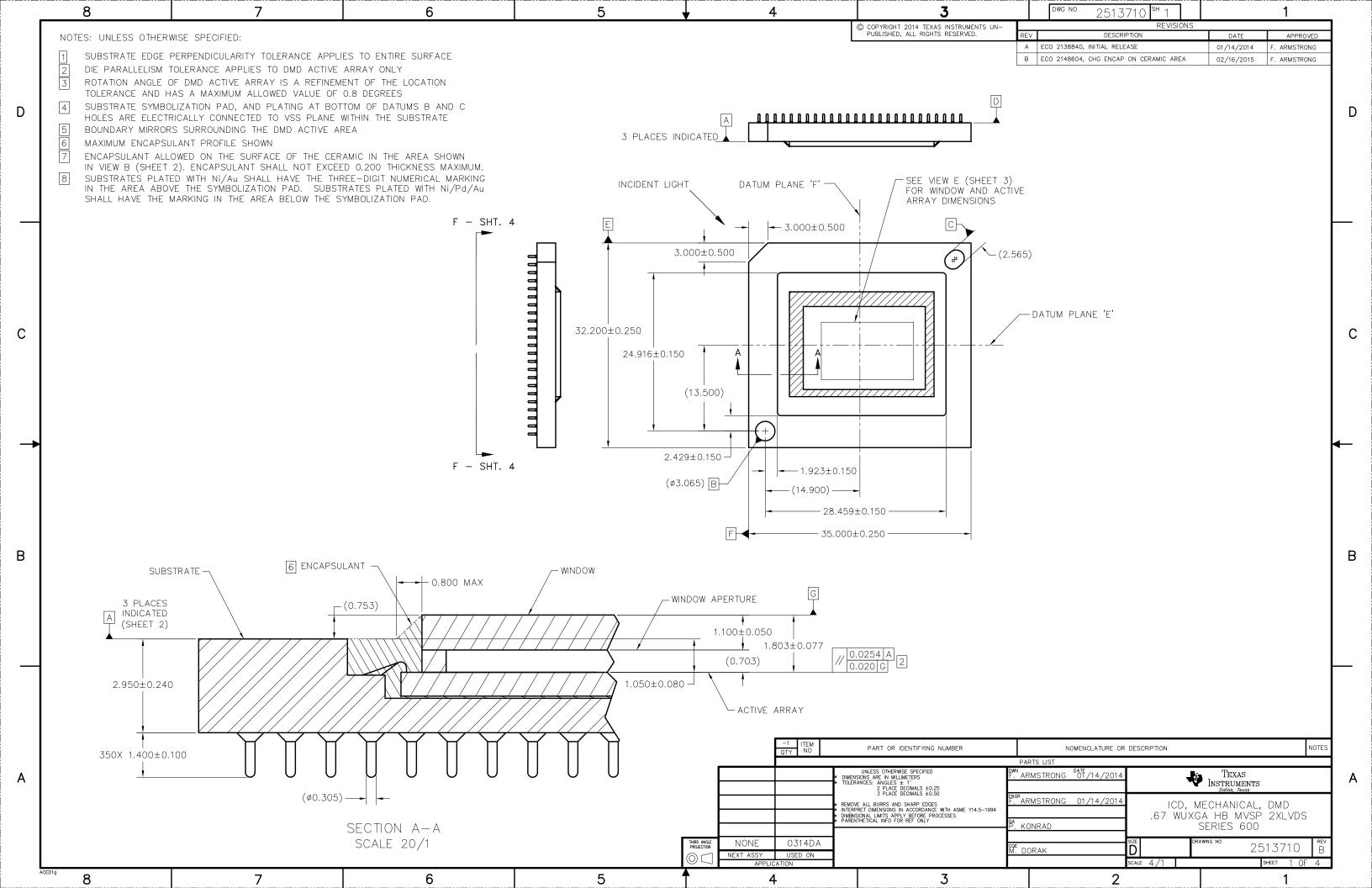
10.8 Glossary

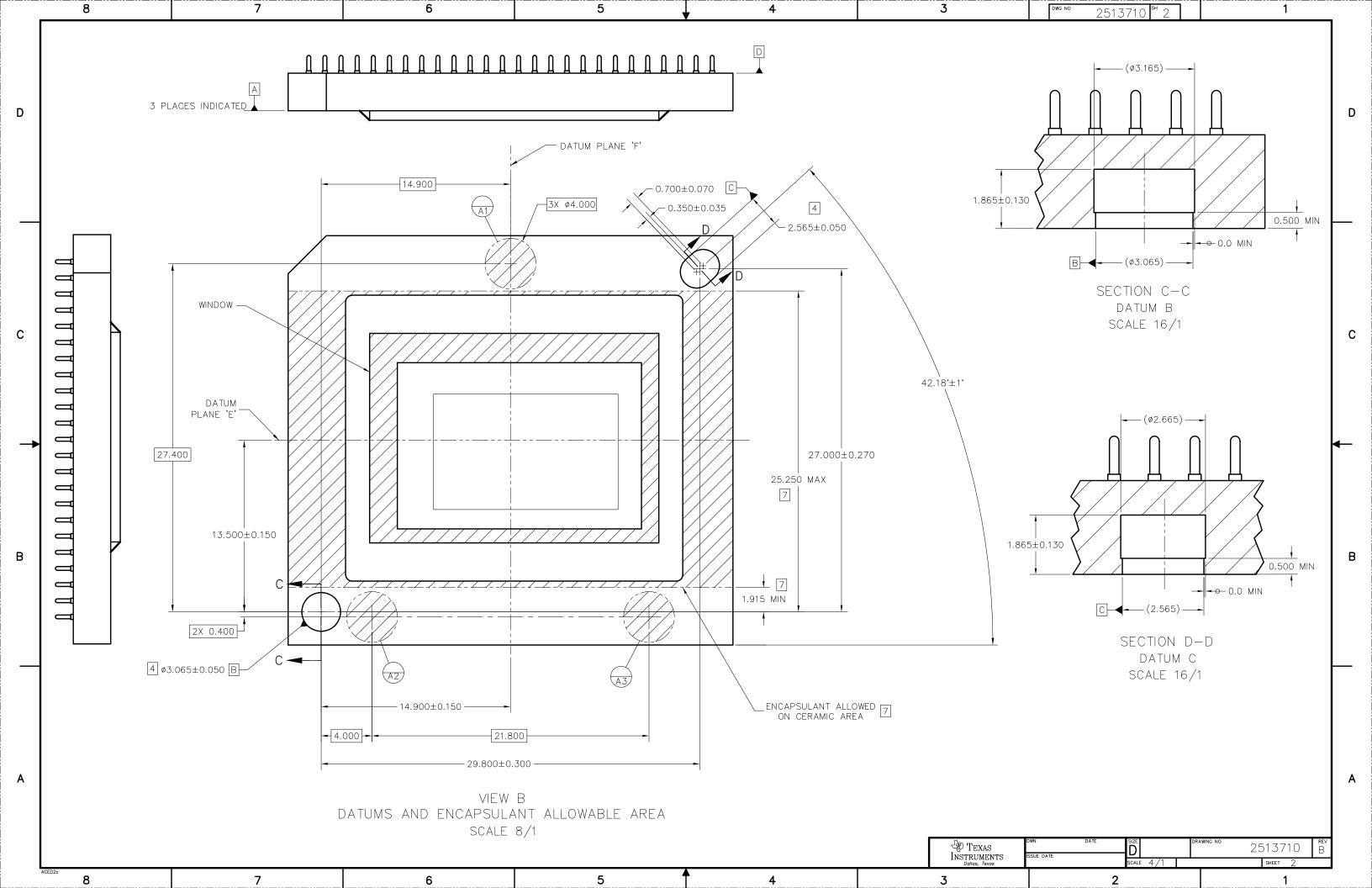
TI Glossary This glossary lists and explains terms, acronyms, and definitions.

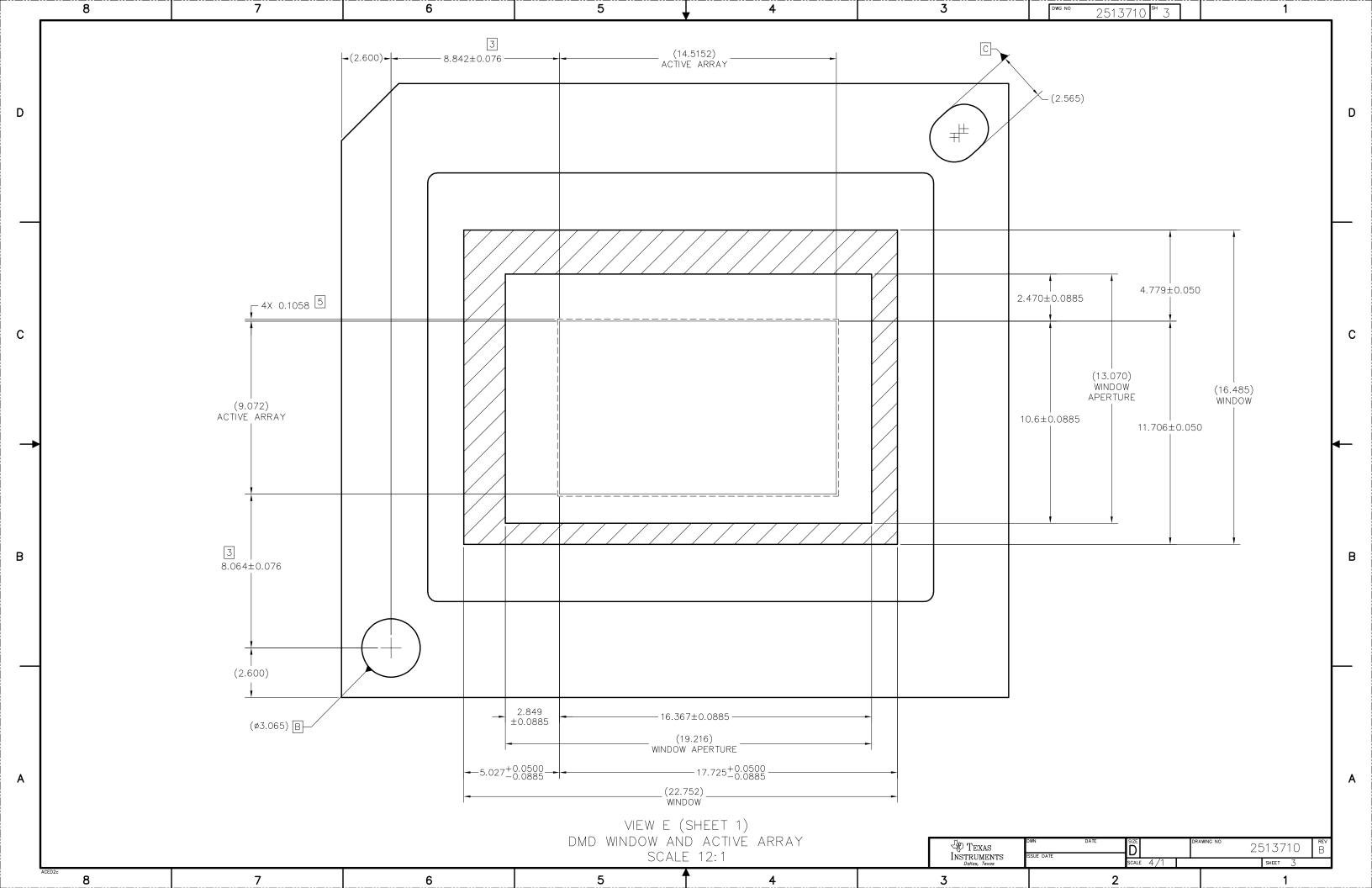
11 Mechanical, Packaging, and Orderable Information

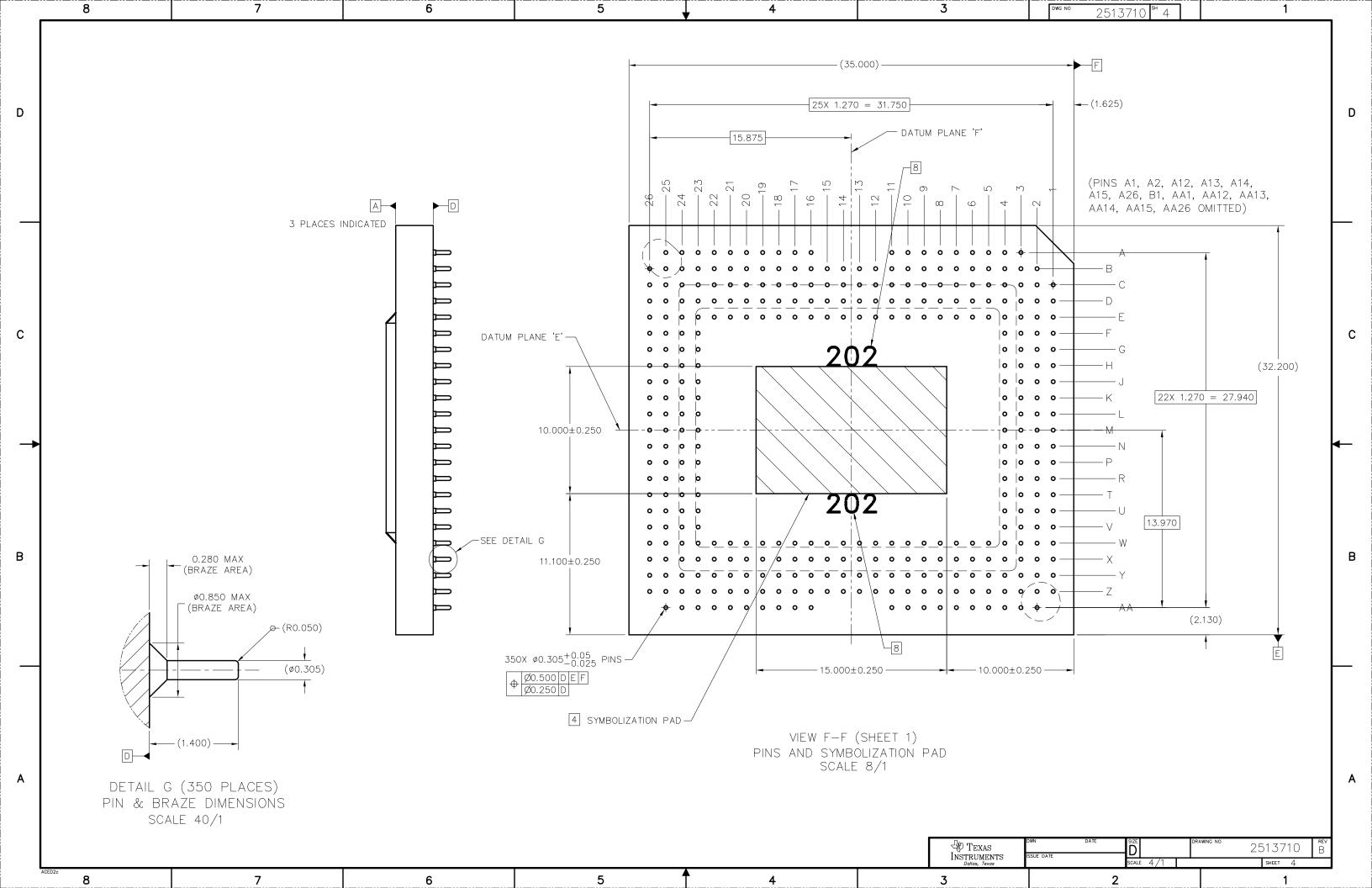
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
DLP670REA0FYE	ACTIVE	CPGA	FYE	350	21	RoHS & Green	NI-PD-AU	N / A for Pkg Type	0 to 70		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

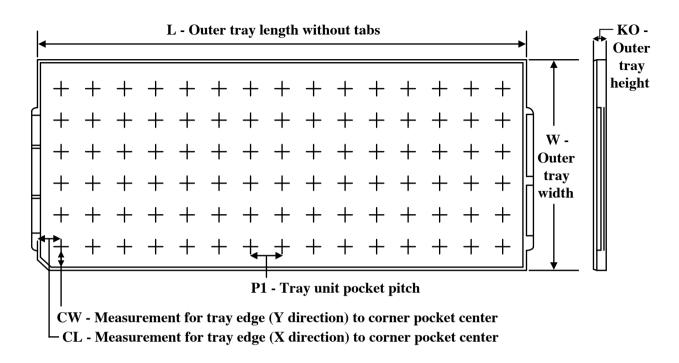
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TRAY



Chamfer on Tray corner indicates Pin 1 orientation of packed units.

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	Κ0 (μm)	P1 (mm)	CL (mm)	CW (mm)
DLP670REA0FYE	FYE	CPGA	350	21	3 x 11	150	315	135.9	12190	27.5	20	27.45

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